

## Dual P-Channel 25-V (G-S) MOSFET

PRODUCT SUMMARY		
$V_{DS}$ (V)	$R_{DS(on)}$ ( $\Omega$ )	$I_D$ (A)
- 30	0.023 at $V_{GS} = - 10$ V	- 7.6
	0.029 at $V_{GS} = - 6$ V	- 6.8

### FEATURES

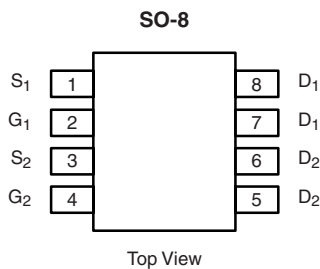
- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET® Power MOSFET
- 25 V  $V_{GS}$  Provides Extra Head Room for Safe Operation
- Compliant to RoHS Directive 2002/95/EC



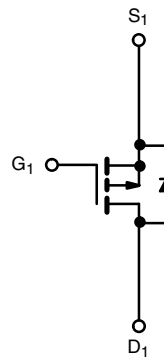
**RoHS**  
COMPLIANT  
HALOGEN  
**FREE**  
Available

### APPLICATIONS

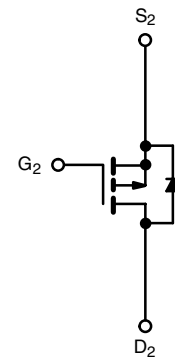
- Notebook
  - Load Switch
  - Battery Charger Switch



**Ordering Information:** Si4973DY-T1-E3 (Lead (Pb)-free)  
Si4973DY-T1-GE3 (Lead (Pb)-free and Halogen-free)



P-Channel MOSFET



P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS $T_A = 25$ °C, unless otherwise noted				
Parameter	Symbol	10 s	Steady State	Unit
Drain-Source Voltage	$V_{DS}$	- 30		V
Gate-Source Voltage	$V_{GS}$	$\pm 25$		
Continuous Drain Current ( $T_J = 150$ °C) <sup>a</sup>	$I_D$	$T_A = 25$ °C	- 7.6	- 5.8
		$T_A = 70$ °C	- 6.1	- 4.6
Pulsed Drain Current	$I_{DM}$	- 30		A
Continuous Source Current (Diode Conduction) <sup>a</sup>	$I_S$	- 1.7	- 0.9	
Maximum Power Dissipation <sup>a</sup>	$P_D$	$T_A = 25$ °C	2.0	1.1
		$T_A = 70$ °C	1.3	0.7
Operating Junction and Storage Temperature Range	$T_J, T_{stg}$	- 55 to 150		°C

THERMAL RESISTANCE RATINGS				
Parameter	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient <sup>a</sup>	$R_{thJA}$	$t \leq 10$ s	45	62.5
		Steady State	85	110
Maximum Junction-to-Foot (Drain)	$R_{thJF}$	26	35	°C/W

Notes:

a. Surface Mounted on 1" x 1" FR4 board.

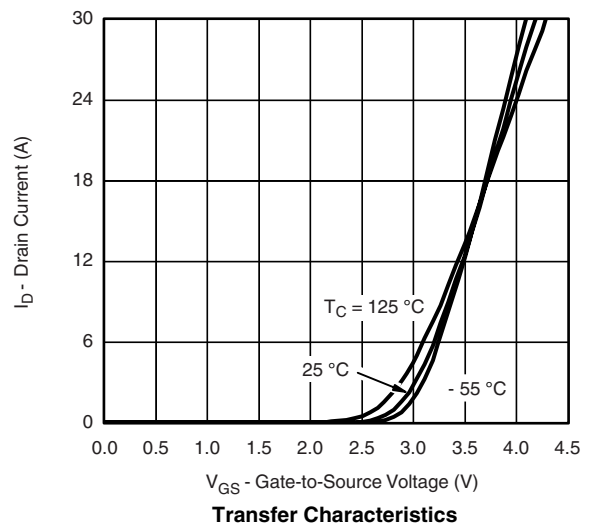
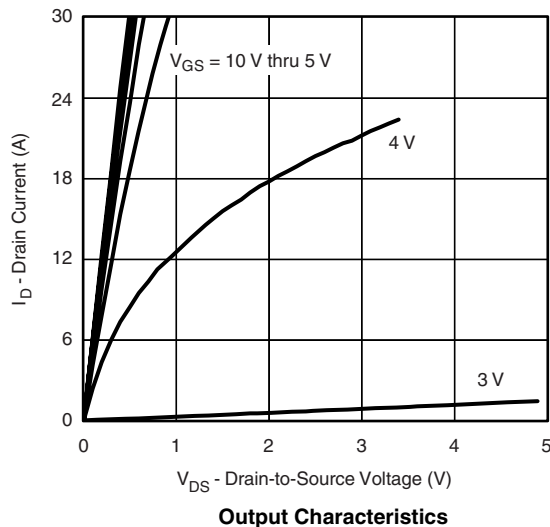
<b>SPECIFICATIONS</b> $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
<b>Static</b>						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\text{ }\mu\text{A}$	-1		-3	V
Gate-Body Leakage	$I_{GSS}$	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			$\pm 100$	nA
		$V_{DS} = 0\text{ V}, V_{GS} = \pm 25\text{ V}$			$\pm 200$	
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = -30\text{ V}, V_{GS} = 0\text{ V}$			-1	$\mu\text{A}$
		$V_{DS} = -30\text{ V}, V_{GS} = 0\text{ V}, T_J = 55\text{ }^\circ\text{C}$			-25	
On-State Drain Current <sup>a</sup>	$I_{D(on)}$	$V_{DS} = -5\text{ V}, V_{GS} = -10\text{ V}$	-30			A
Drain-Source On-State Resistance <sup>a</sup>	$R_{DS(on)}$	$V_{GS} = -10\text{ V}, I_D = -7.6\text{ A}$		0.018	0.023	$\Omega$
		$V_{GS} = -6\text{ V}, I_D = -6.8\text{ A}$		0.023	0.029	
Forward Transconductance <sup>a</sup>	$g_{fs}$	$V_{DS} = -10\text{ V}, I_D = -7.6\text{ A}$		22		S
Diode Forward Voltage <sup>a</sup>	$V_{SD}$	$I_S = -1.7\text{ A}, V_{GS} = 0\text{ V}$		-0.8	-1.2	V
<b>Dynamic<sup>b</sup></b>						
Total Gate Charge	$Q_g$	$V_{DS} = -15\text{ V}, V_{GS} = -10\text{ V}, I_D = -7.6\text{ A}$		37	56	nC
Gate-Source Charge	$Q_{gs}$			6		
Gate-Drain Charge	$Q_{gd}$			11		
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = -15\text{ V}, R_L = 15\text{ }\Omega$ $I_D = -1\text{ A}, V_{GEN} = -10\text{ V}, R_g = 6\text{ }\Omega$		10	15	ns
Rise Time	$t_r$			15	25	
Turn-Off Delay Time	$t_{d(off)}$			115	180	
Fall Time	$t_f$			90	140	
Source-Drain Reverse Recovery Time	$t_{rr}$	$I_F = -1.7\text{ A}, di/dt = 100\text{ A}/\mu\text{s}$		80	120	

Notes:

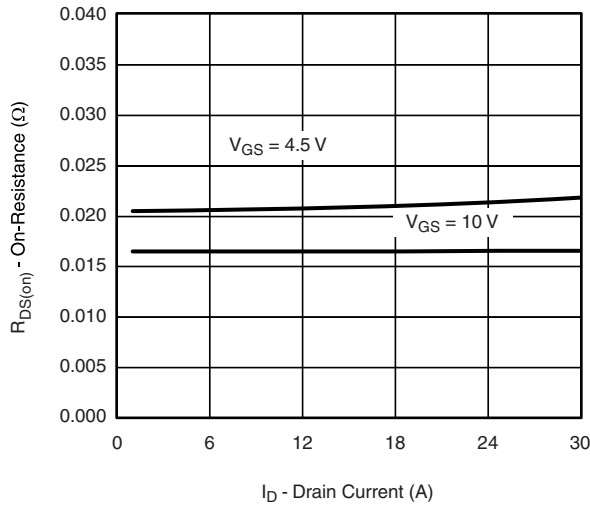
- a. Pulse test; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$ .
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

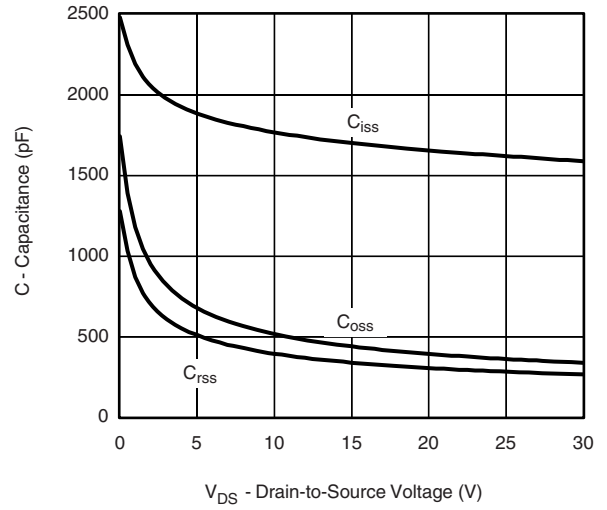
## TYPICAL CHARACTERISTICS $25\text{ }^\circ\text{C}$ , unless otherwise noted



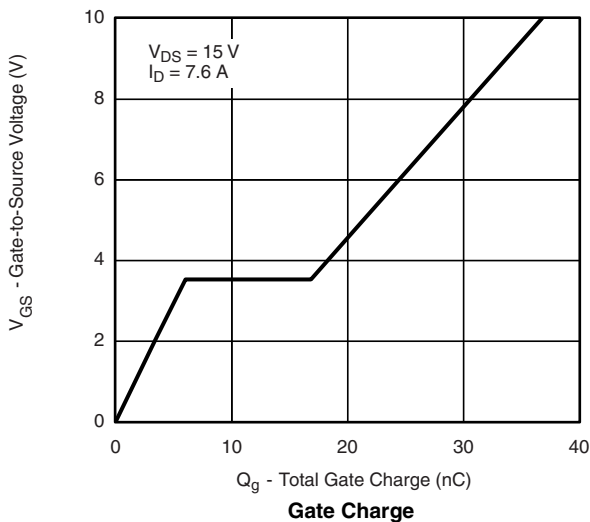
**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted



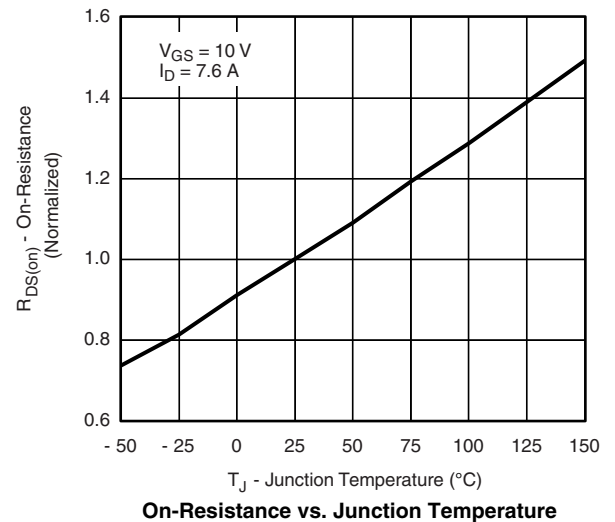
**On-Resistance vs. Drain Current**



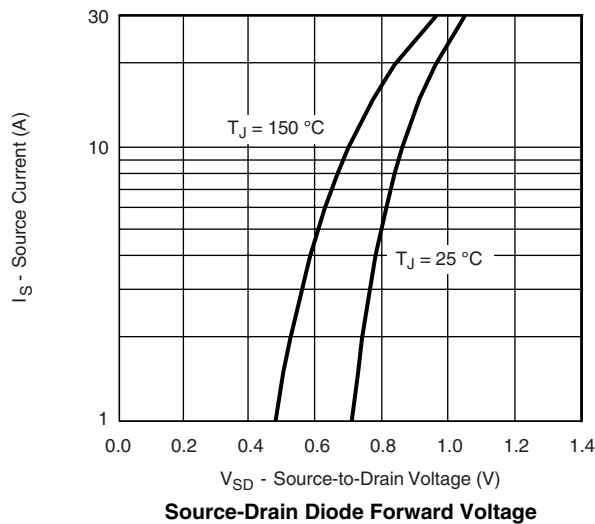
**Capacitance**



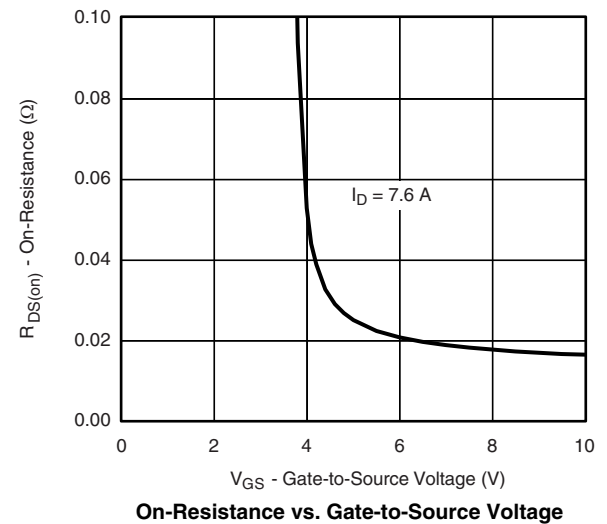
**Gate Charge**



**On-Resistance vs. Junction Temperature**

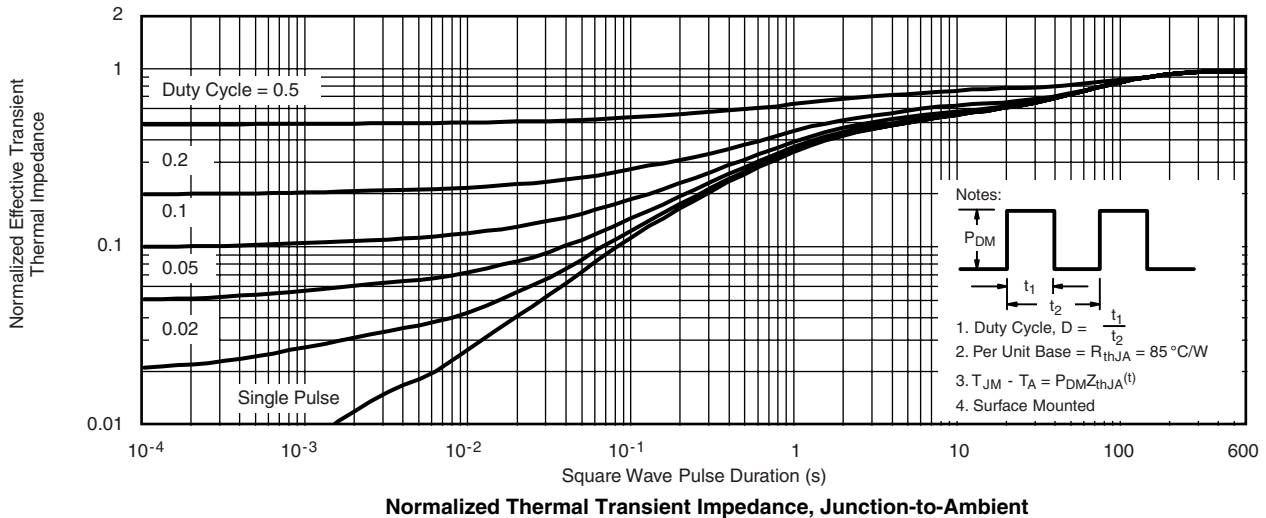
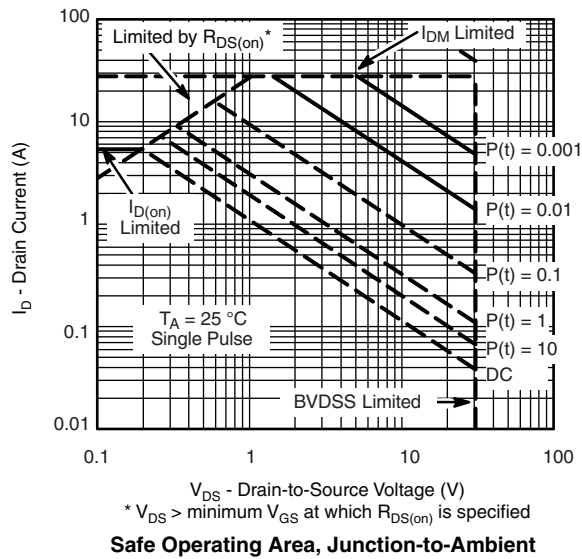
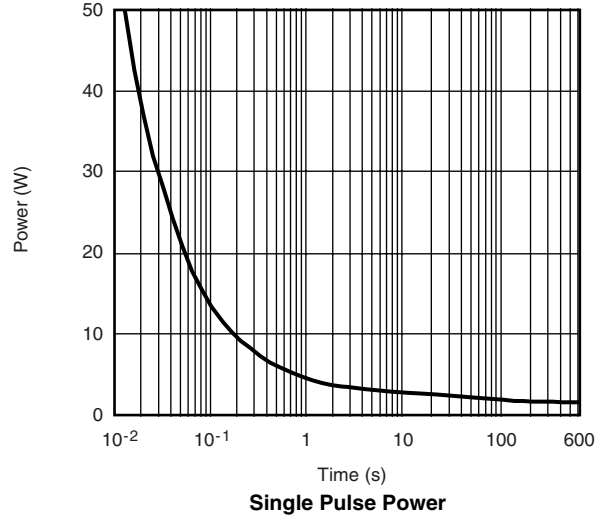
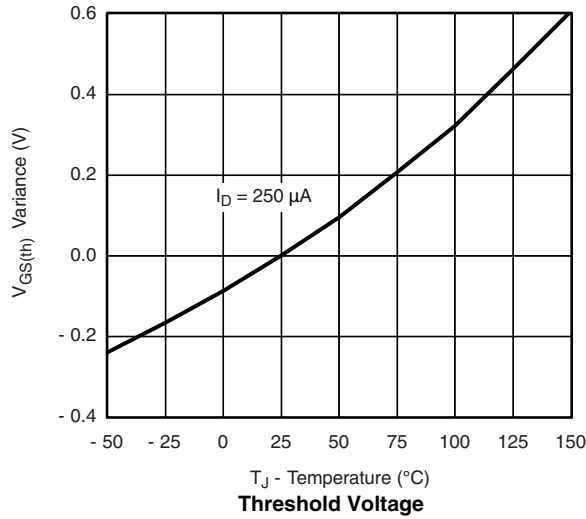


**Source-Drain Diode Forward Voltage**



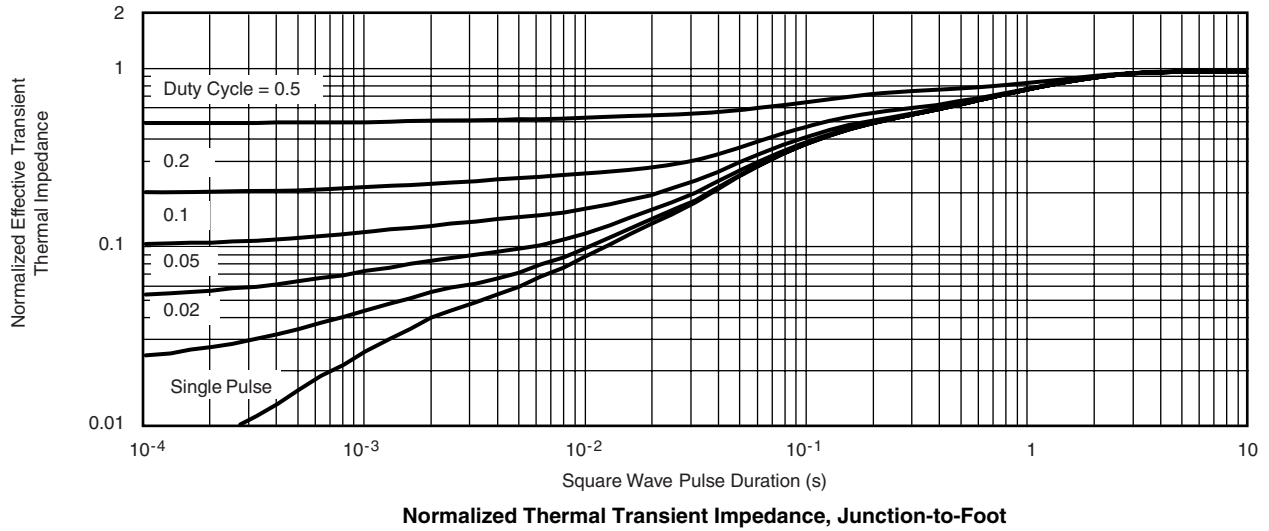
**On-Resistance vs. Gate-to-Source Voltage**

**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted





**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted



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